

SIEMENS

HYB 514171 BJ/BJL -60/-70

256k x 16 - Bit Dynamic RAM

INFORMATION NOTE NO.4

256kx16 WORDWIDE DYNAMIC MEMORIES
(Hypershrink Version)

CHARACTERISATION DATA

5.95

infowd4.doc

This information note is intended to provide technical information on the SIEMENS 256kx16 DYNAMIC ACCESS MEMORIES (Hypershrink-Version) HYB 514171BJ/BJL.

CHARACTERISTICS OF DC - PARAMETERS

The SIEMENS HYB 514171BJ/BJL 256kx16 worldwide DRAM device ("Hypershrink Version") is guaranteed to meet certain DC parametric limits over the temperature range 0° to 70°C. This information note shows the actual performance levels that can typically be expected from devices. Samples out of three different production lots have been randomly selected and characterised.

Typical values of operation and standby currents as a function of temperature, voltage and cycle time are shown in fig.1 through fig 10.

In fig.11 and 12 the typical behaviour of V_{IHmin} (minimum TTL-level input high voltage) , V_{ILmax} (maximum TTL-level input low voltage), V_{OH}/V_{OL} (output high and low voltage) as a function of supply voltage is shown.

CHARACTERISTICS OF AC - PARAMETERS

Supply voltage and temperature dependence of row (trac), column (tcac), address (taa) and output enable (toea) access times are the topics of fig.13 and fig. 16.

All other AC - parameters measured at two voltages (VCC = 4.5 V and 5.5 V) and two temperatures (+85°C and - 10°C) are put together in tables 1 & 2.

All measurements shown in this information note have been performed on an ADVANTEST 3333 dedicated memory test system.

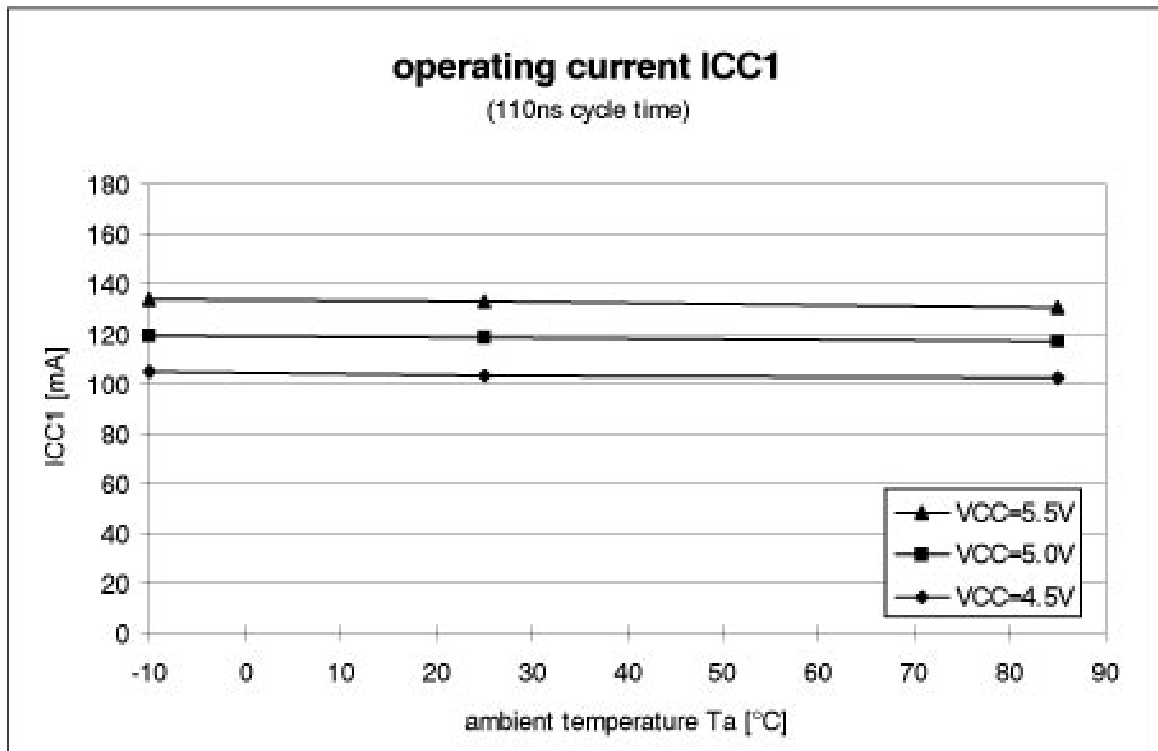


fig.1

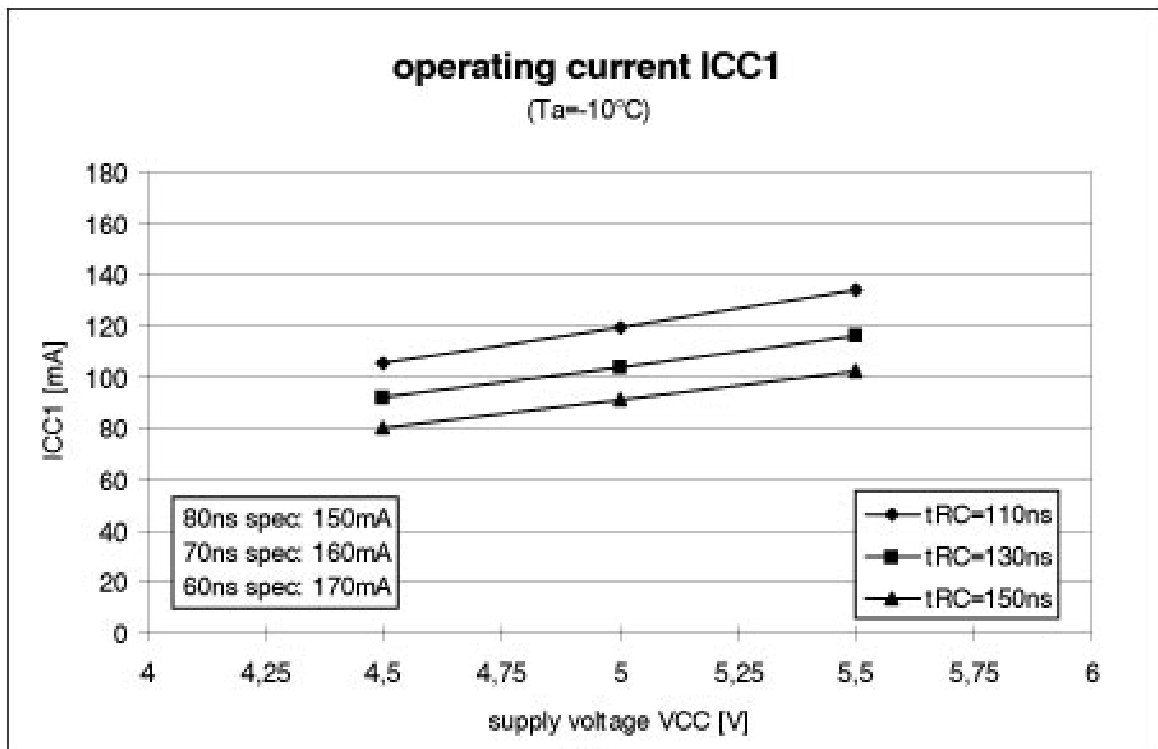


fig.2

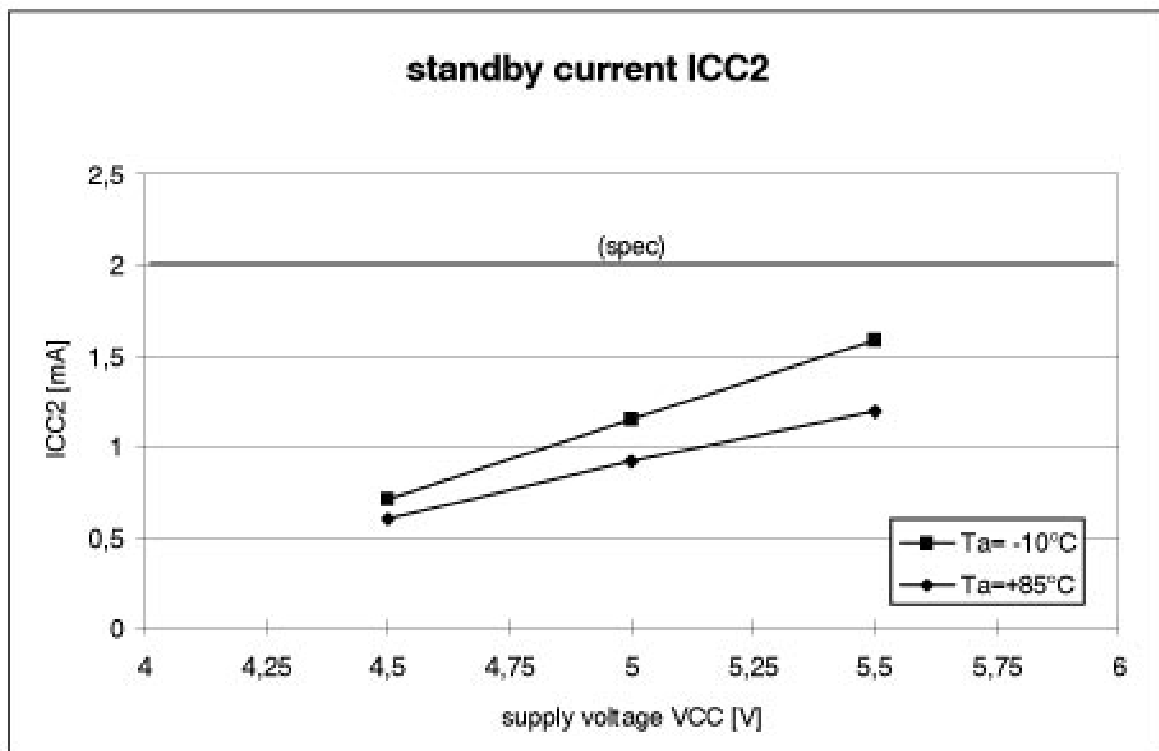


fig.3

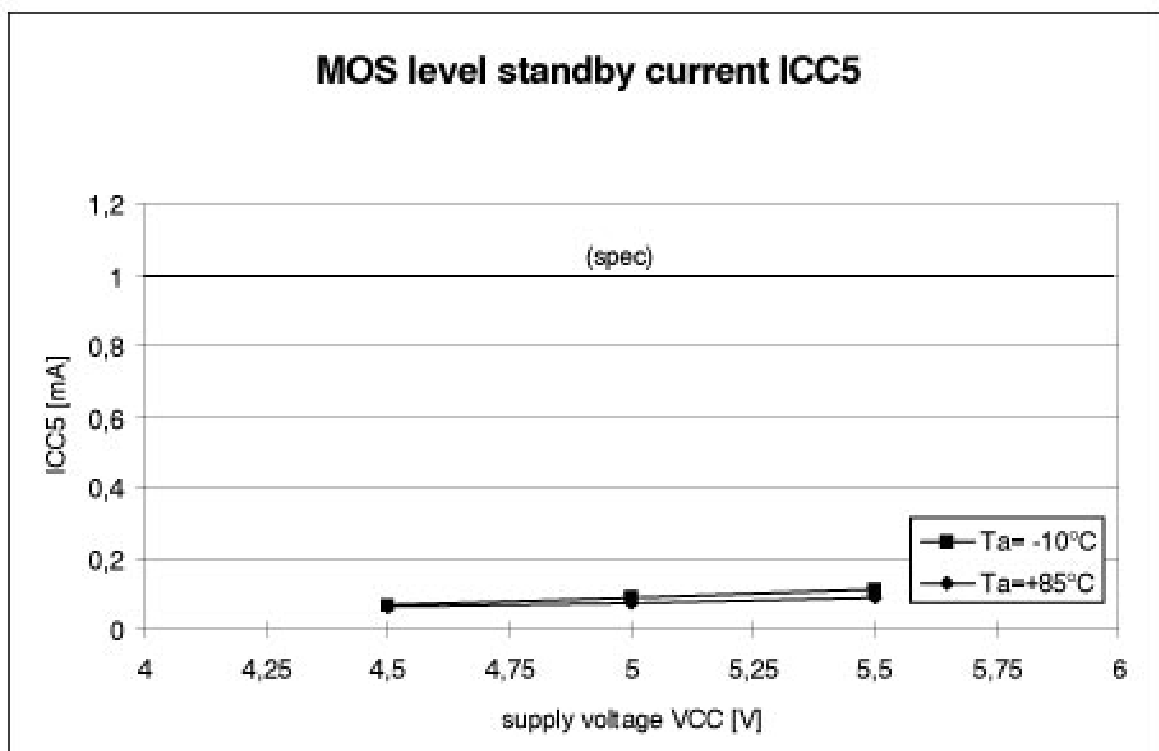


fig.4

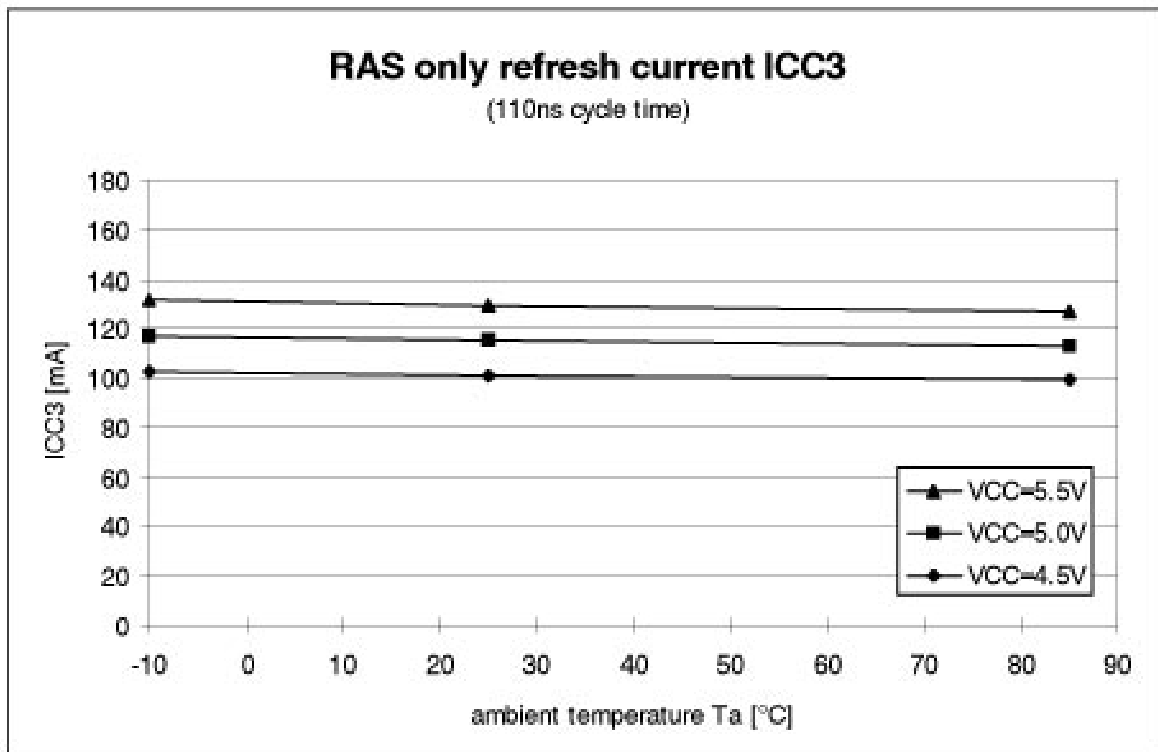


fig.5

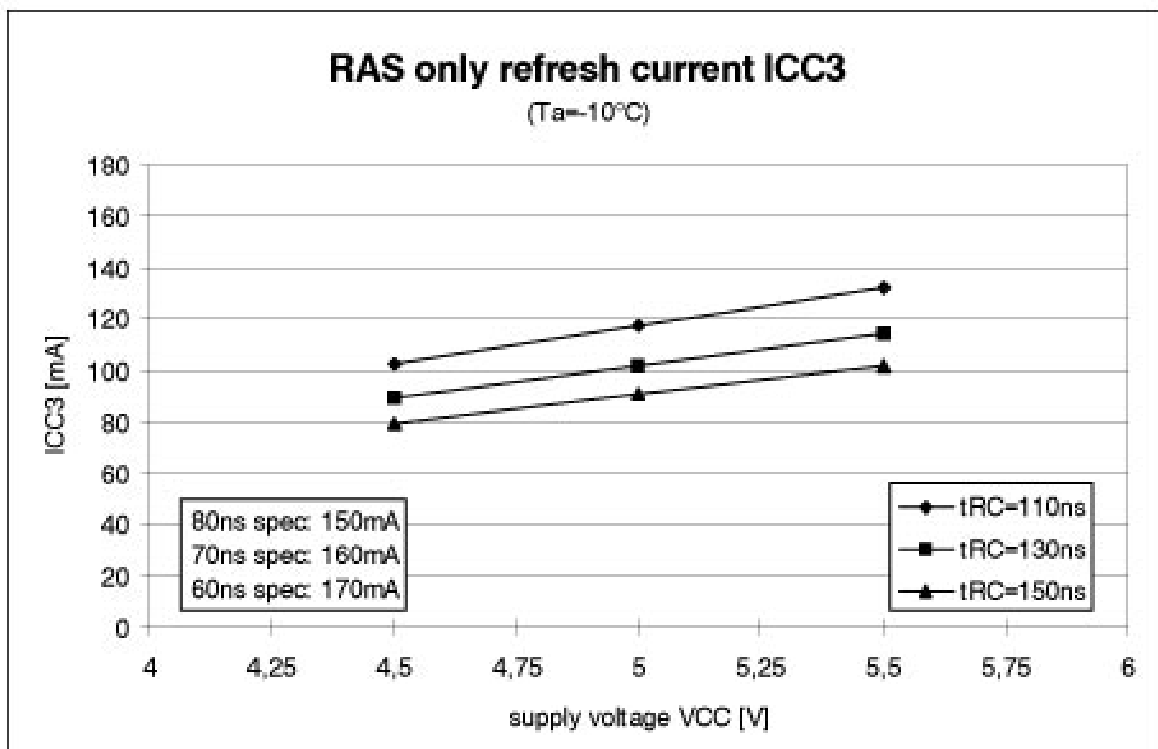


fig.6

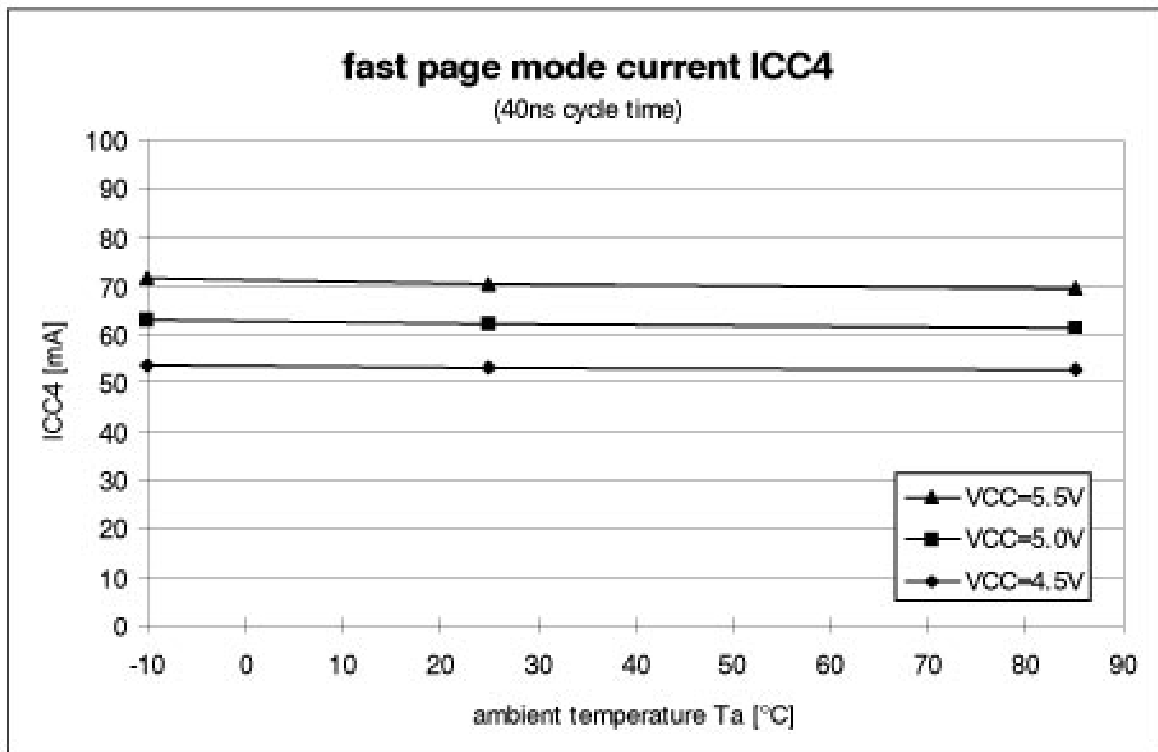


fig.7

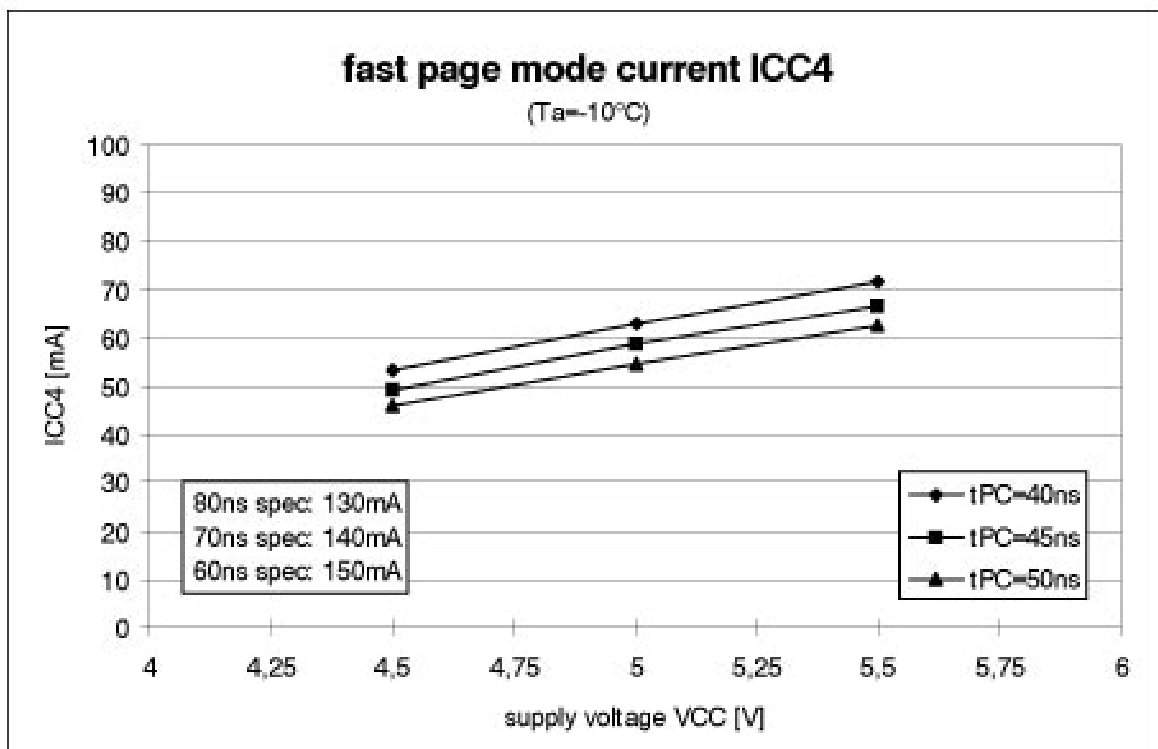


fig.8

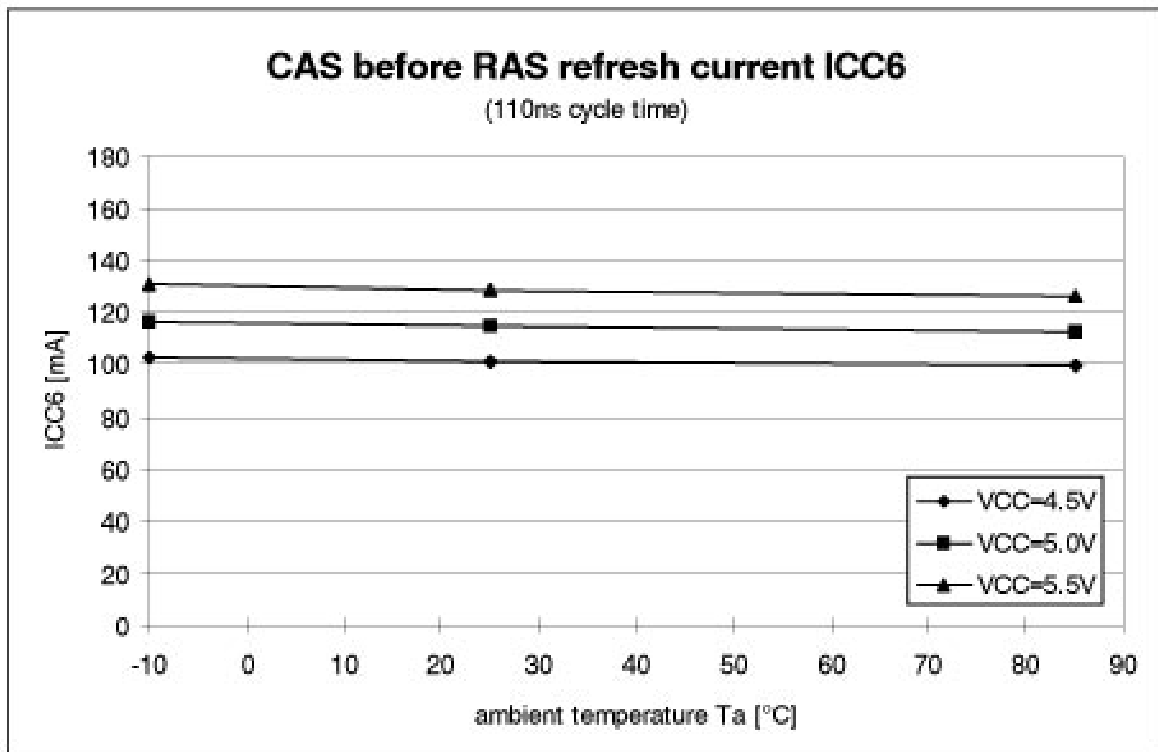


fig.9

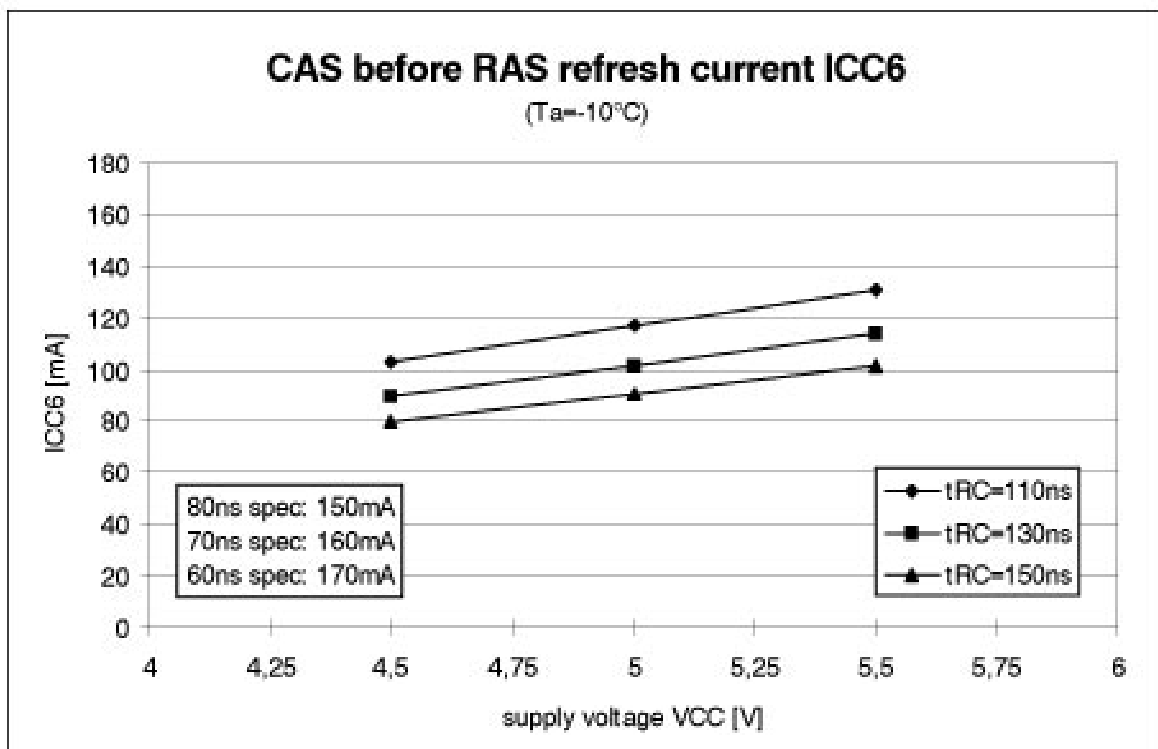


fig.10

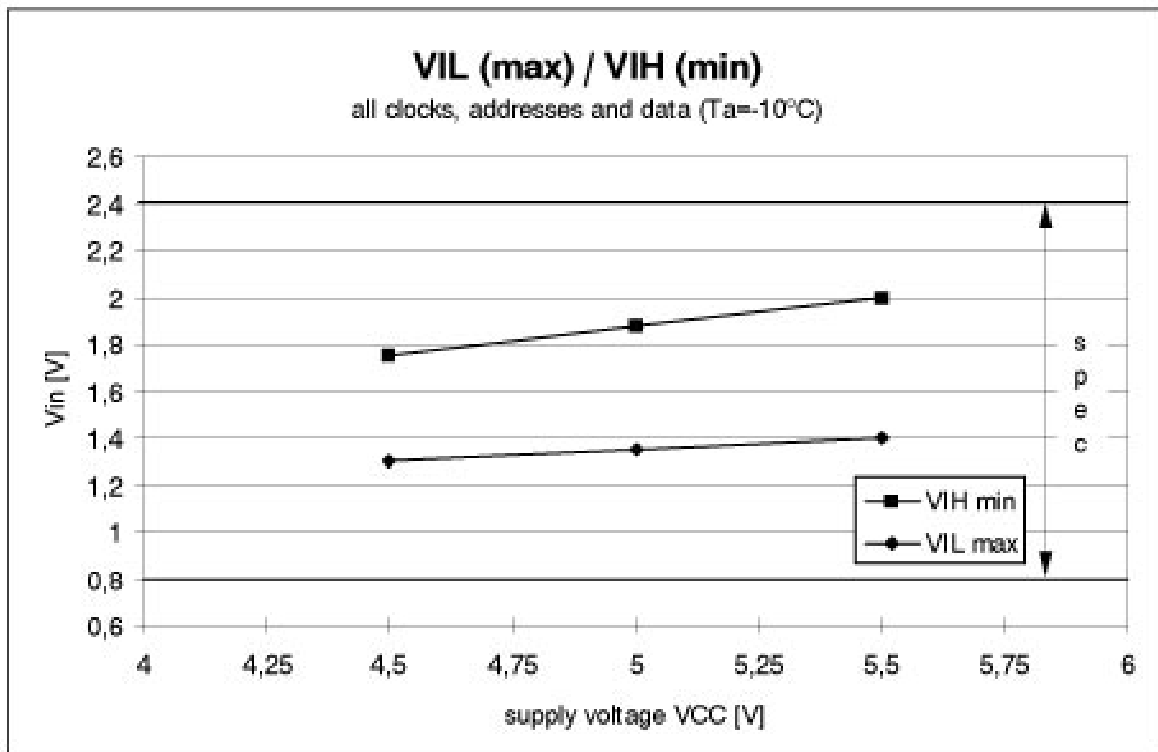


fig.11

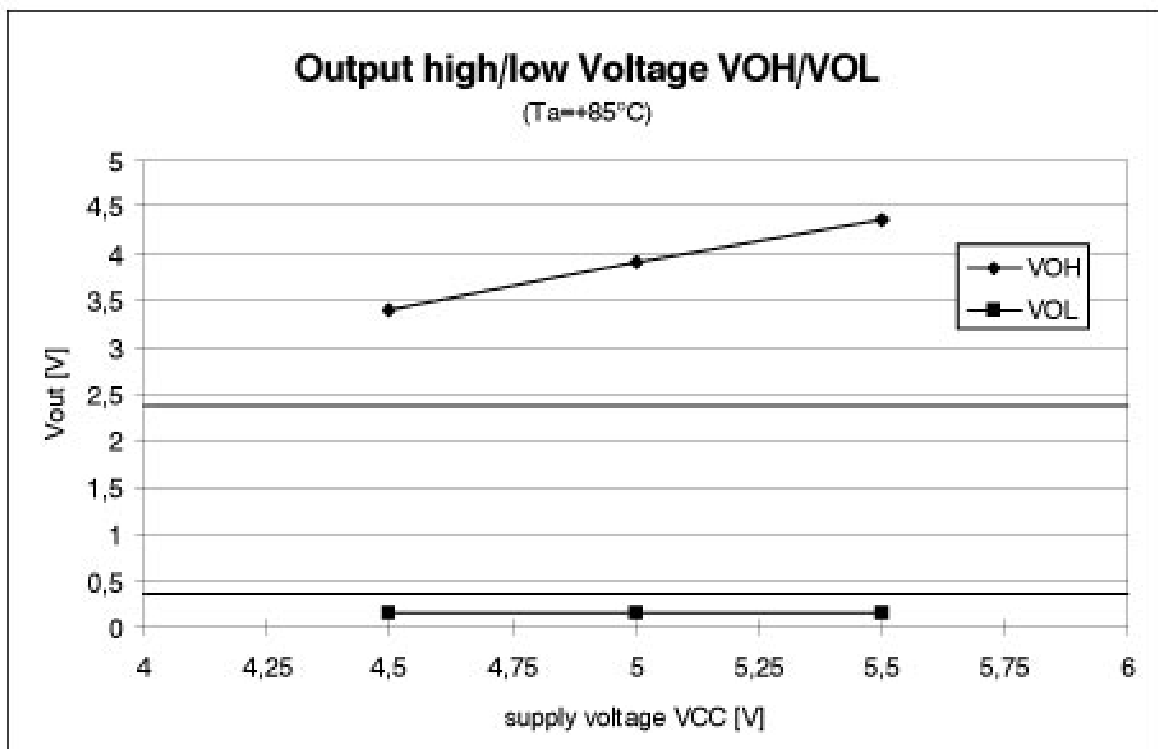


fig.12

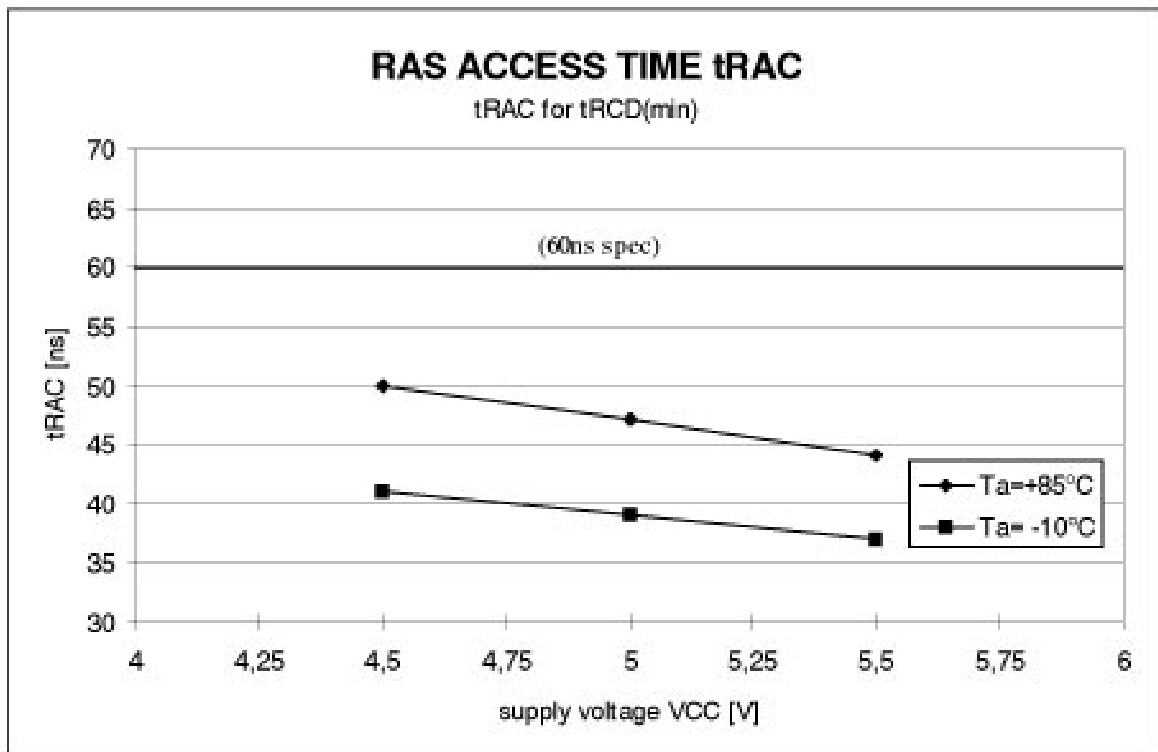


fig.13

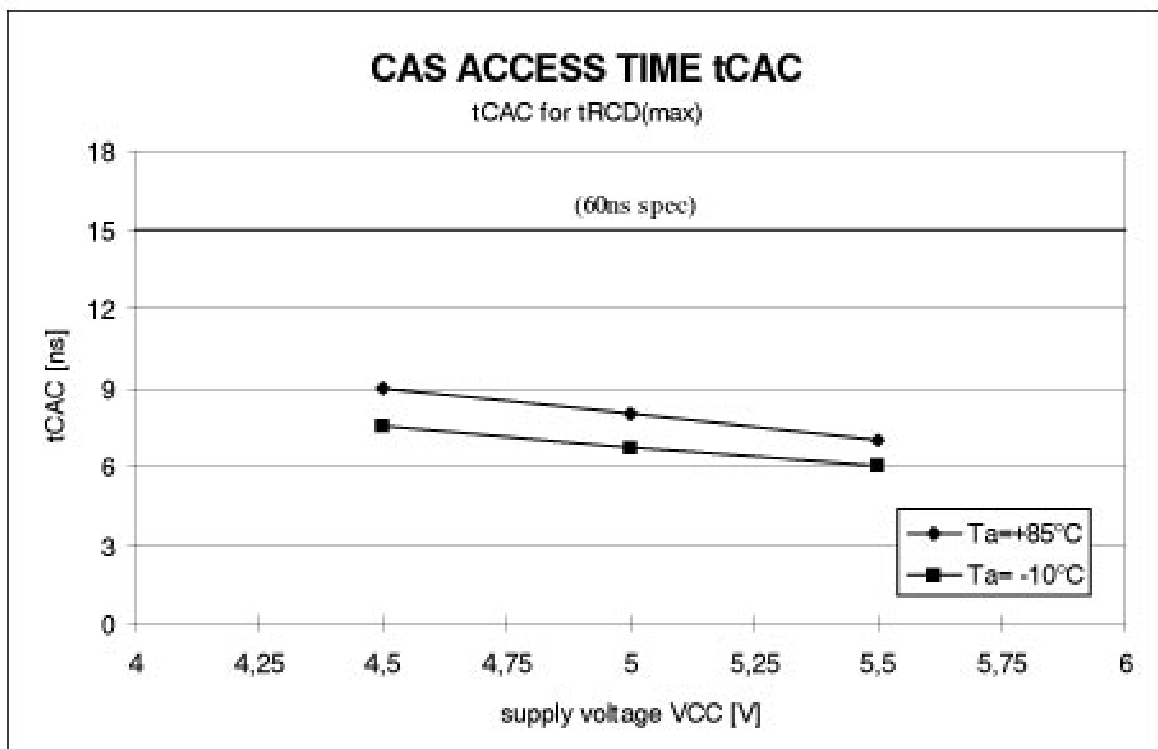


fig.14

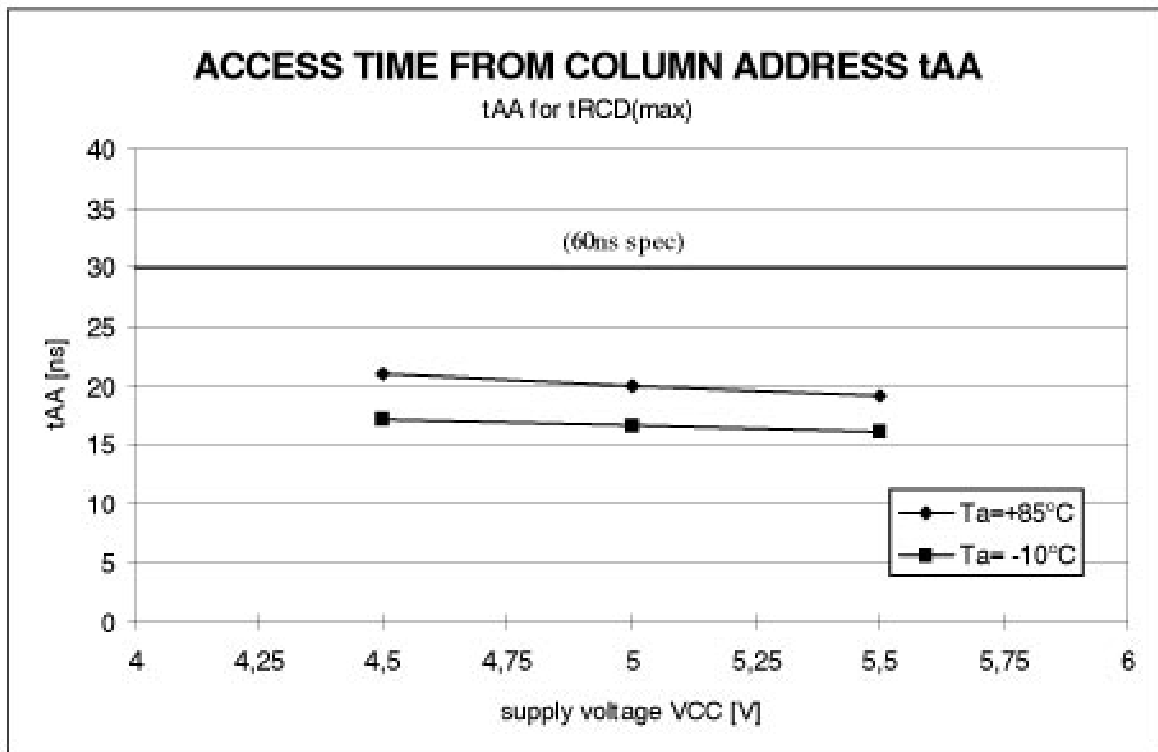


fig.15

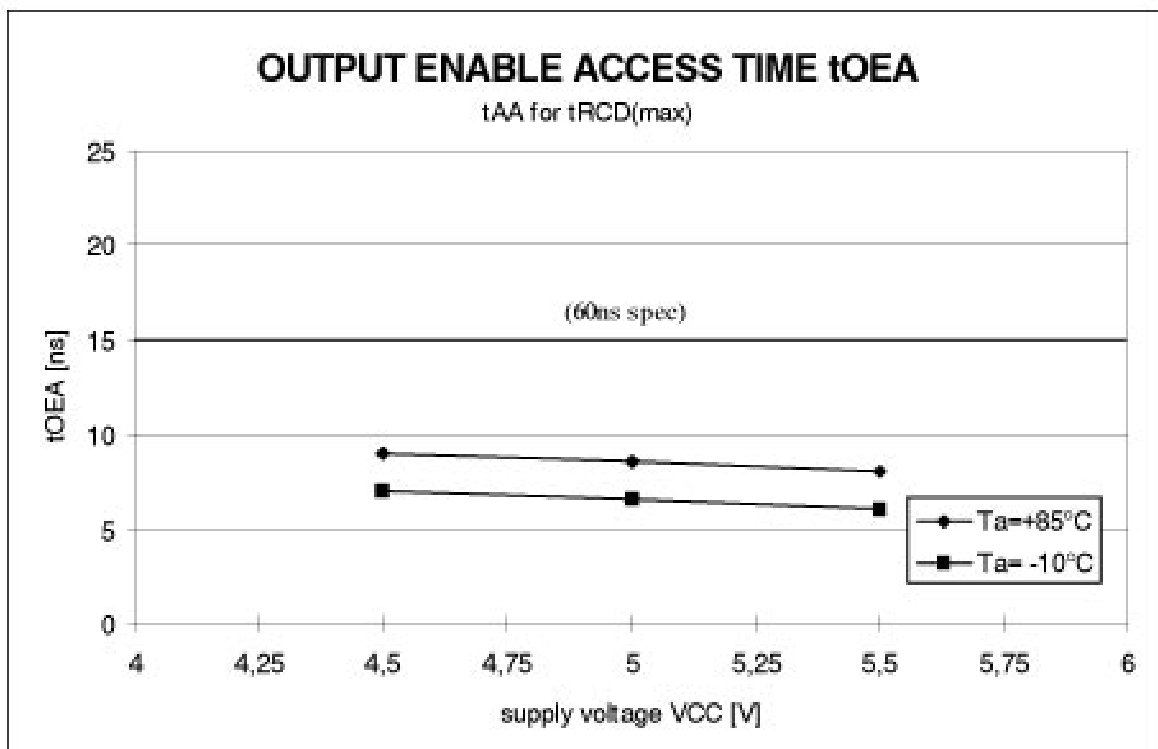


fig.16

AC CHARACTERISTICS

Device: 256K X 16 DRAM 60ns

COMMON PARAMETERS

Parameter	Spec -60ns	Measurement	(T = 5ns)
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	Unit [ns]		Ta = -10°C		Ta = +85°C		note
	min.	max.	Vcc = 4.5V	Vcc = 5.5V	Vcc = 4.5V	Vcc = 5.5V	
trc	110	-	74	70	86	78	1)
trp	40	-	15	12	21	17	
tras	60	10000	23	19	29	24	2)
tcas	15	10000	2	0	4	2	3)
tasr	0	-	-7	-6	-9	-8	
trah	10	-	-1	-1	1	0	
tasc	0	-	-9	-8	-10	-9	
tcsh	15	-	2	1	3	2	
tar	55	-	<=25	<=25	26	<=25	
trcd (min)	20		2	3	4	4	
trcd (max)	-	45	34	31	41	37	4)
trad	15	30	4	4	6	5	
trsh	15	-	0	0	1	1	
tcsh	50	-	36	32	45	39	
torp	5	-	-4	-4	-5	-4	
troh	10	-	-6	-6	-6	-6	
toez	0	20	5	5	7	6	

READ CYCLE

	Unit [ns]		Ta = -10°C		Ta = +85°C	
	min.	max.	Vcc = 4.5V	Vcc = 5.5V	Vcc = 4.5V	Vcc = 5.5V
trac	-	60	41	37	50	44
tcac	-	15	7	6	9	7
taa	-	30	17	16	21	19
toea	-	15	7	6	9	8
trcs	0	-	-7	-7	-8	-7
trch	0	-	-8	-7	-9	-8
trrh	0	-	-6	-6	-7	-6
tral	30	-	6	<=5	7	6
toff	0	20	4	3	5	4

WRITE CYCLE

	Unit [ns]		Ta = -10°C		Ta = +85°C	
	min.	max.	Vcc = 4.5V	Vcc = 5.5V	Vcc = 4.5V	Vcc = 5.5V
twcs	0	-	-5	-5	-5	-5
twch	10	-	-1	-2	0	-1
twp	10	-	-2	-2	-1	-2
trwl	15	-	-1	-1	0	0
tcwl	15	-	2	1	4	3
tds	0	-	-9	-8	10	-9
tdh	15	-	2	1	4	3
twcr	50	-	19	18	20	19
tdhr	50	-	22	21	24	23

tab. 1

READ-MODIFY-WRITE CYCLE

	Unit [ns]		Ta = -10°C		Ta = +85°C	
	min.	max.	Vcc = 4.5V	Vcc = 5.5V	Vcc = 4.5V	Vcc = 5.5V
trwc	160	-	97	91	110	101
trwd	90	-	47	42	53	49
tcwd	45	-	12	12	13	12
tawd	60	-	22	22	24	24

note

REFRESH CYCLE

CAS-BEFORE-RAS CYCLE

	Unit [ns]		Ta = -10°C		Ta = +85°C	
	min.	max.	Vcc = 4.5V	Vcc = 5.5V	Vcc = 4.5V	Vcc = 5.5V
tcsr	5	-	-4	-4	-4	-4
tchr	10	-	-4	-4	-3	-4
trpc	0	-	-8	-7	-9	-7
tcpr	10	-	1	1	1	1

FAST PAGE MODE CYCLE

	Unit [ns]		Ta = -10°C		Ta = +85°C	
	min.	max.	Vcc = 4.5V	Vcc = 5.5V	Vcc = 4.5V	Vcc = 5.5V
tpc	40	-	<=32	<=32	<=32	<=32
top	10	-	-4	-4	-4	-4
trasp	60	200000	23	19	29	24
tcpa	-	35	21	19	24	22
tprwc	90	-	44	42	49	45

2)

**CAS-BEFORE-RAS COUNTER TEST
CYCLE**

	Unit [ns]		Ta = -10°C		Ta = +85°C	
	min.	max.	Vcc = 4.5V	Vcc = 5.5V	Vcc = 4.5V	Vcc = 5.5V
tcpt	30	-	-1	-1	-1	-1

Notes:

- 1) *all AC-parameters are measured with 0.85V/2.35V levels on clocks and addresses*
- 2) *the "min."-value is shown*
- 3) *tcas(min)-value in a write cycle is shown*
- 4) *trod(max.) is the reference point where the access time is controlled by toac*